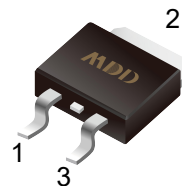


V_{DS}	500V
$I_D(T_C=25^{\circ}C)$	5A
$R_{DS(on),max}$	1.6 Ω @ $V_{GS}=10V$
$Q_{g,typ}$	12.8nC

TO-252



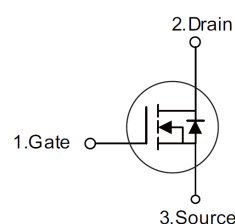
General Features

- ◆ Low $R_{DS(on)}$
- ◆ Low gate charge
- ◆ 100% UIS tested
- ◆ RoHS compliant

Application

- ◆ Electronic ballast
- ◆ Switched mode power supplies.
- ◆ UPS.

Equivalent Circuit



Absolute Maximum Ratings ($T_A=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	500	V
Gate-Source Voltage	V_{GS}	± 30	V
Continuous Drain Current	I_D	5	A
Pulsed Drain Current(Note 1)	I_{DM}	20	A
Avalanche Energy Single Pulsed (Note 2)	E_{AS}	210	mJ
Peak Diode Recovery dv/dt (Note 3)	dv/dt	5	V/ns
Power Dissipation	P_D	75	W
Junction Temperature	T_J	150	$^{\circ}C$
Storage Temperature	T_{stg}	-55 ~150	$^{\circ}C$

Thermal Characteristics

Parameter	Symbol	Value	Unit
		TO-252	
Thermal resistance, Junction-to-case	$R_{\theta JC}$	1.67	$^{\circ}C/W$
Thermal resistance, Junction-to-ambient	$R_{\theta JA}$	110	$^{\circ}C/W$

- Notes:**
1. Pulse width limited by maximum junction temperature.
 2. $L=10mH$, $I_{AS} = 6.5A$, Starting $T_J = 25^{\circ}C$.
 3. $I_{SD} = 5A$, $di/dt \leq 100A/\mu s$, $V_{DD} \leq BV_{DS}$, Starting $T_J = 25^{\circ}C$.

Ta = 25°C unless otherwise specified

Symbol	Parameter		Condition	Min	Typ	Max	Unit
V_{(BR)DSS}	Drain-Source Breakdown Voltage		V_{GS}=0V, I_D=250μA	500	--	--	V
I_{gss}	Gate-Source Leakage Current	Forward	V_{GS}=30V, V_{DS}=0V	--	--	100	nA
		Reverse	V_{GS}=-30V, V_{DS}=0V	--	--	-100	nA
I_{DSS}	Drain-Source Leakage Current		V_{DS}=500V, V_{GS}=0V	--	--	1	uA
V_{GS(TH)}	Gate Threshold Voltage		V_{DS}=V_{GS}, I_D=250μA	2.0	--	4.0	V
R_{DS(ON)}	Drain-Source On-State Resistance		V_{GS}=10V, I_D=2.5A	--	1.35	1.6	Ω

Dynamic Electrical Characteristics

Symbol	Parameter	Condition	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	V_{DS}=25V V_{GS}=0V f=1MHz	--	537.5	--	pF
C_{oss}	Output Capacitance		--	80.3	--	pF
C_{rss}	Reverse Transfer Capacitance		--	4	--	pF
Q_g	Total Gate Charge	V_{DS}=400V, V_{GS}=10V, I_D=5A (Note1,2)	--	12.8	--	nC
Q_{gs}	Gate Source Charge		--	3.9	--	nC
Q_{gd}	Gate Drain Charge		--	4.6	--	nC

Switching Characteristics

Symbol	Parameter	Condition	Min	Typ	Max	Unit
t_{d(on)}	Turn on Delay Time	V_{DS}=250V, I_D=5A, R_G=10Ω (Note1,2)	--	10.3	--	ns
t_r	Turn on Rise Time		--	33.1	--	ns
t_{d(off)}	Turn Off Delay Time		--	29.4	--	ns
t_f	Turn Off Fall Time		--	13.2	--	ns

Source Drain Diode Characteristics

Symbol	Parameter	Condition	Min	Typ	Max	Unit
I_{SD}	Source drain current(Body Diode)		--	--	5	A
I_{SM}	Pulsed Current		--	--	20	A
V_{SD}	Drain-Source Diode Forward Voltage	I_S=5A, V_{GS}=0V	--	--	1.5	V
t_{rr}	Body Diode Reverse Recovery Time	V_R=250V I_F=5A, -diF/dt =100A/μs	--	319.2	--	ns
Q_{rr}	Body Diode Reverse Recovery Charge		--	1.6	--	uC

Notes:

- 1.Pulse test ; Pulse width≤300us, duty cycles≤2%.
- 2.Essentially independent of operating temperature.

Electrical Characteristics Diagrams

Figure 1. Typical Output Characteristics

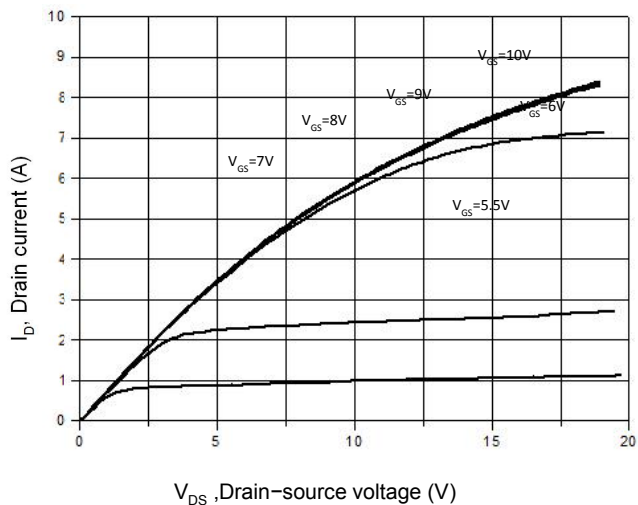


Figure 2. Transfer Characteristics

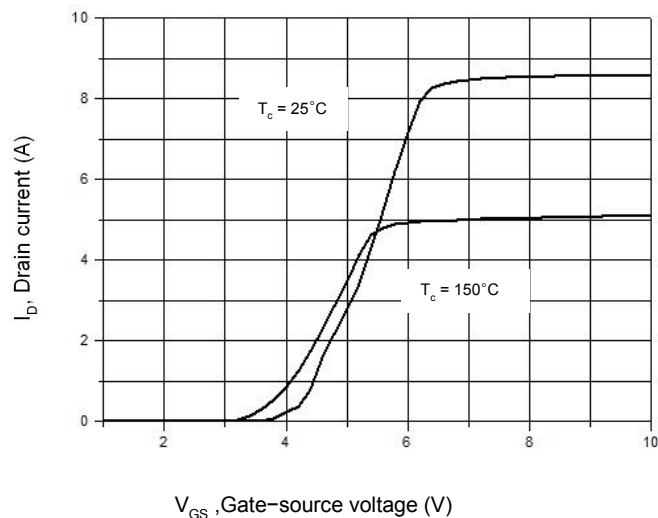


Figure 3. On-Resistance Variation vs. Drain Current

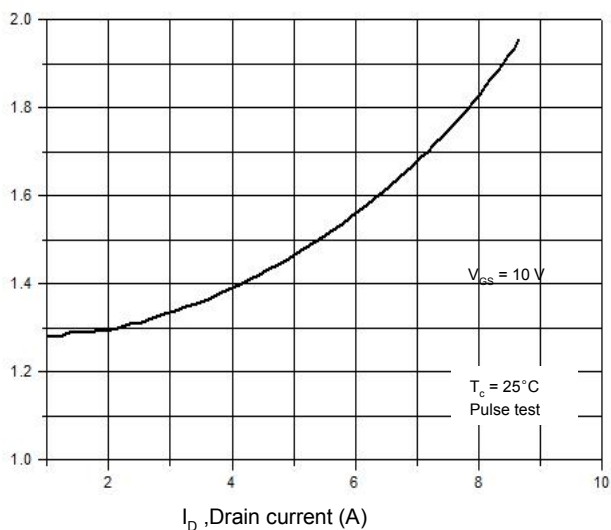


Figure 4. Threshold Voltage vs. Temperature

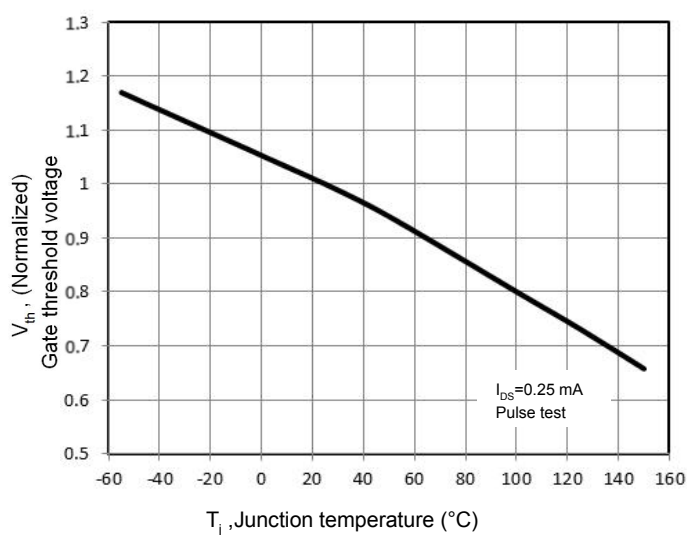


Figure 5. Breakdown Voltage vs. Temperature

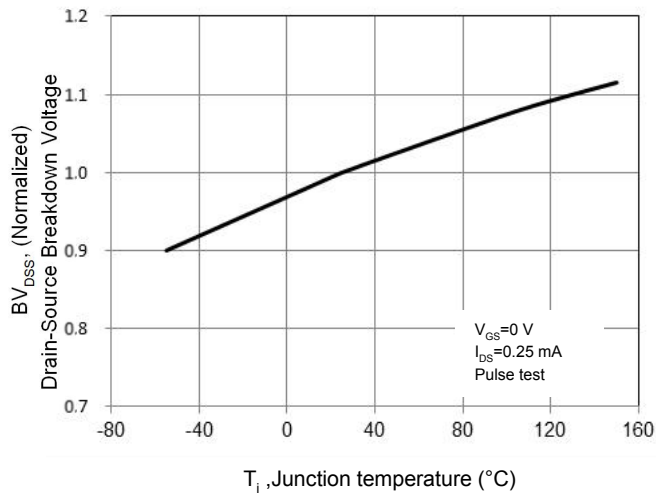


Figure 6. On-Resistance vs. Temperature

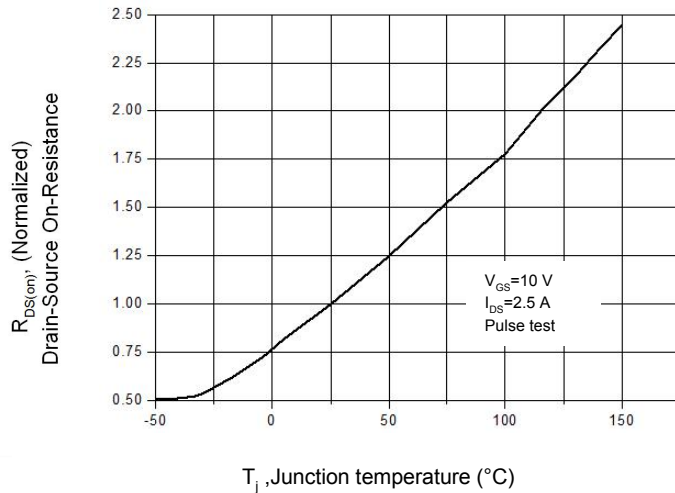


Figure 7. Capacitance Characteristics

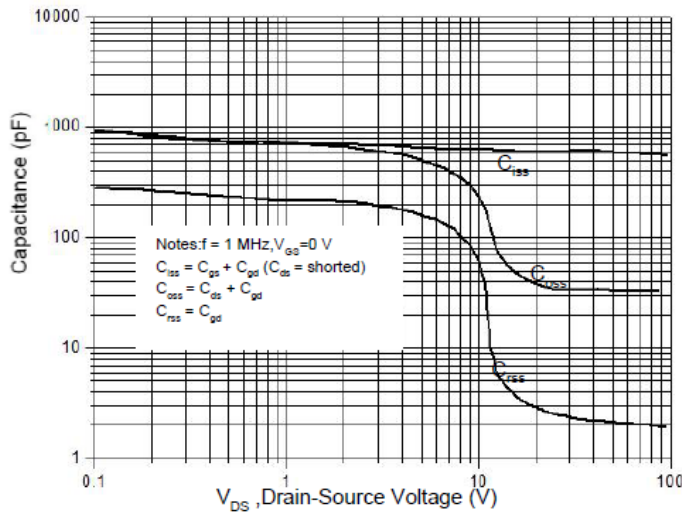


Figure 8. Gate Charge Characteristics

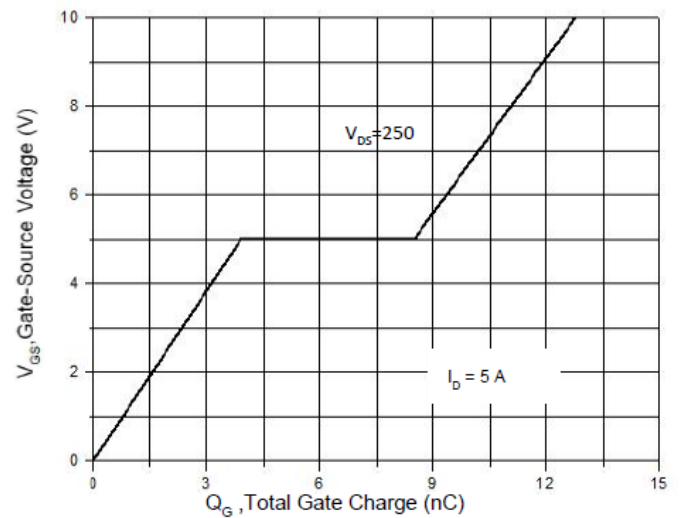


Figure 9. Maximum Safe Operating Area
TO-220F

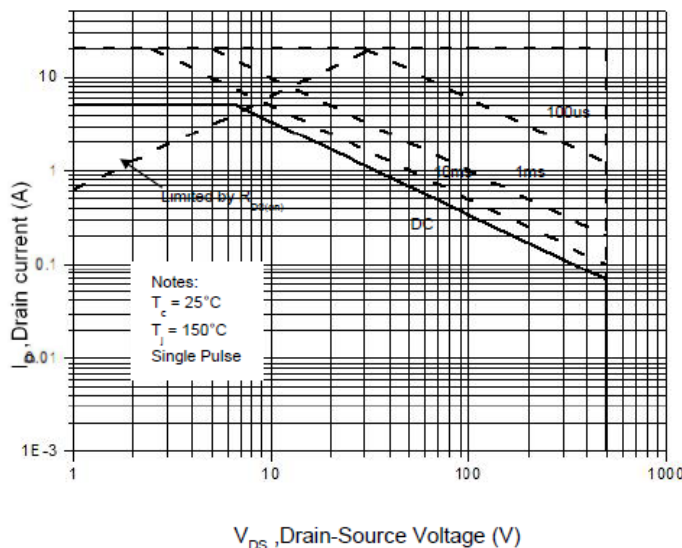


Figure 11. Power Dissipation vs. Temperature
TO-220F

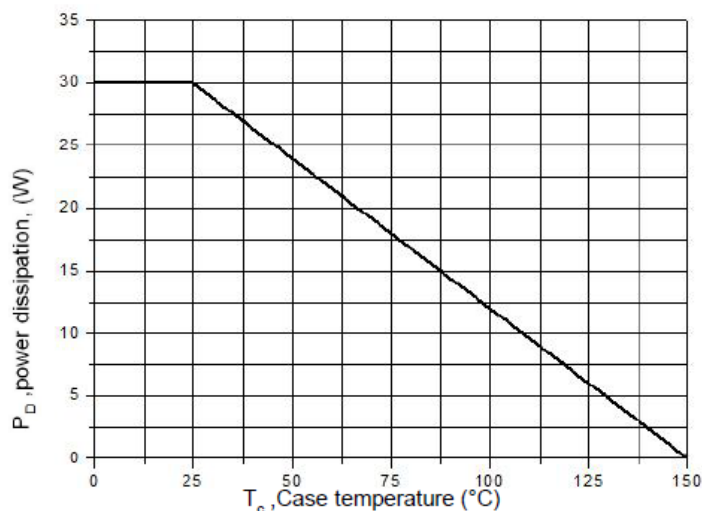


Figure 10. Maximum Safe Operating Area
TO-220/TO-252

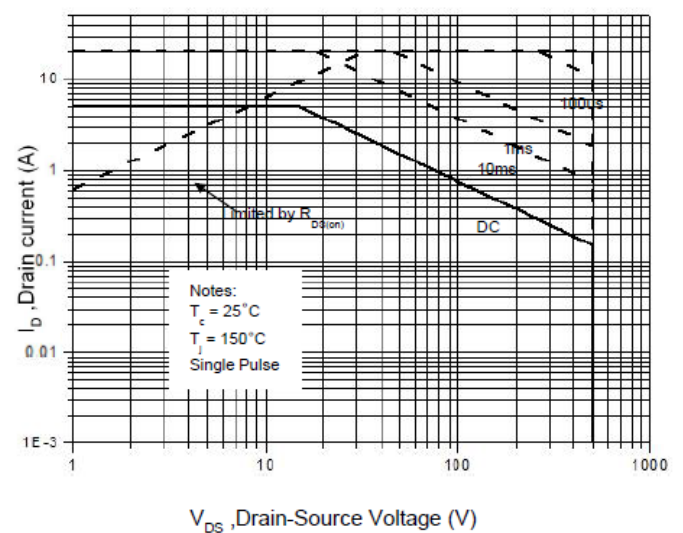


Figure 12. Power Dissipation vs. Temperature
TO-220/TO-252

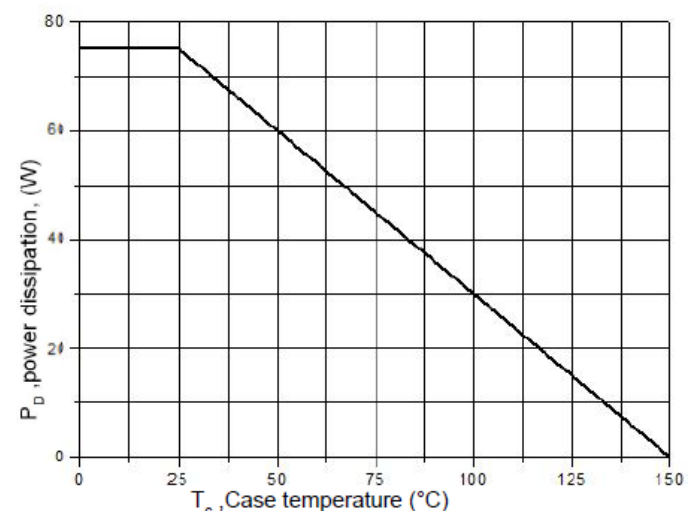
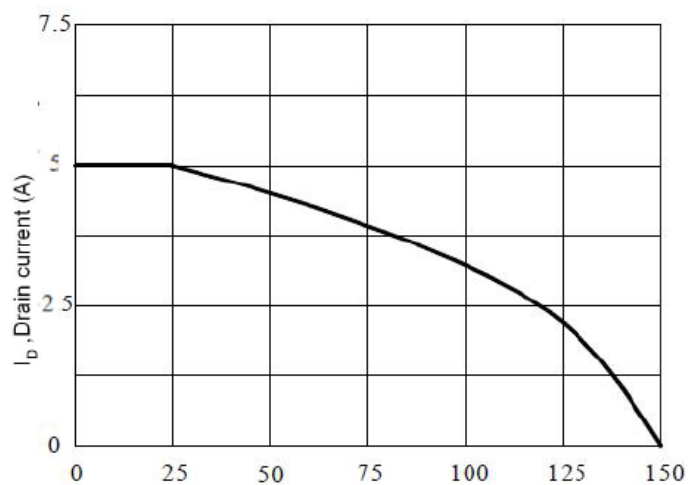
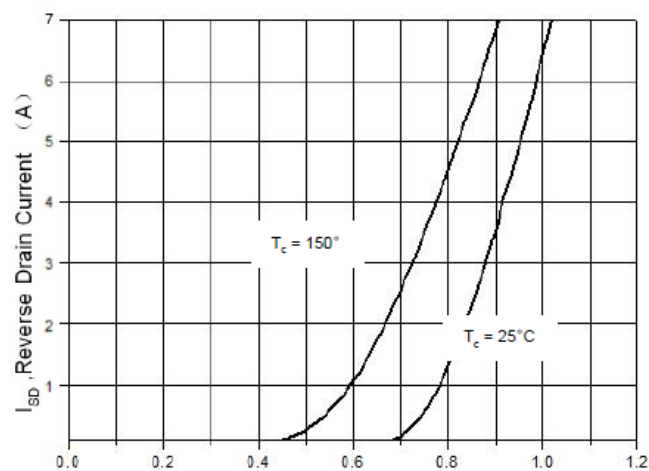


Figure 13. Continuous Drain Current vs. Temperature



T_c , Case temperature (°C)

Figure 14. Body Diode Transfer Characteristics



V_{SD} , Source-Drain Voltage (V)

Figure 15 Transient Thermal Impedance, Junction to Case, TO-220F

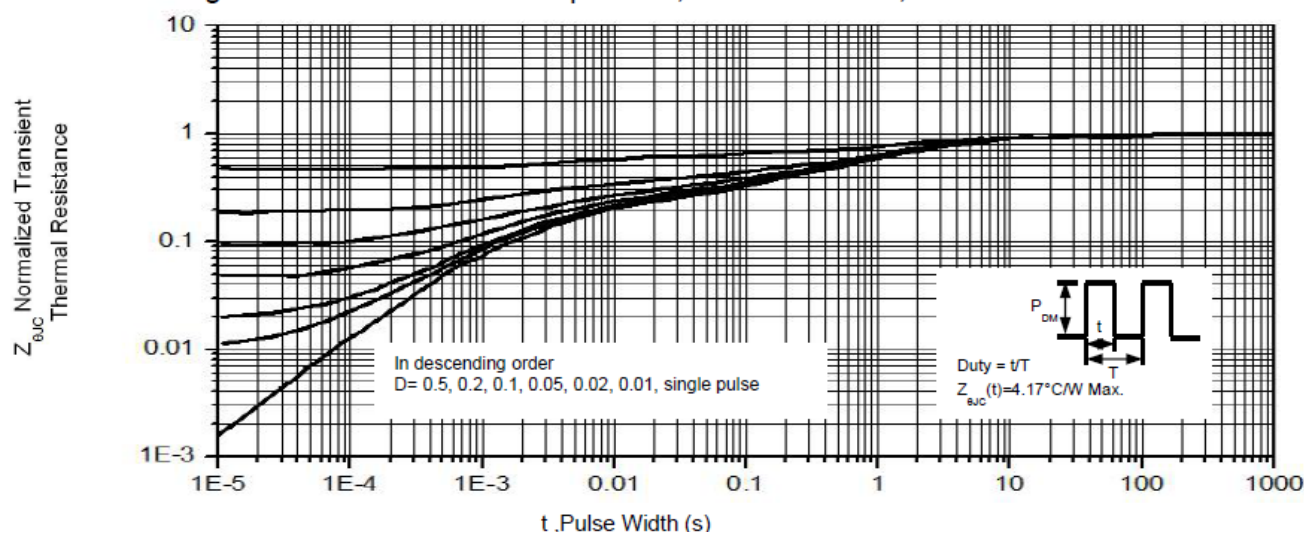
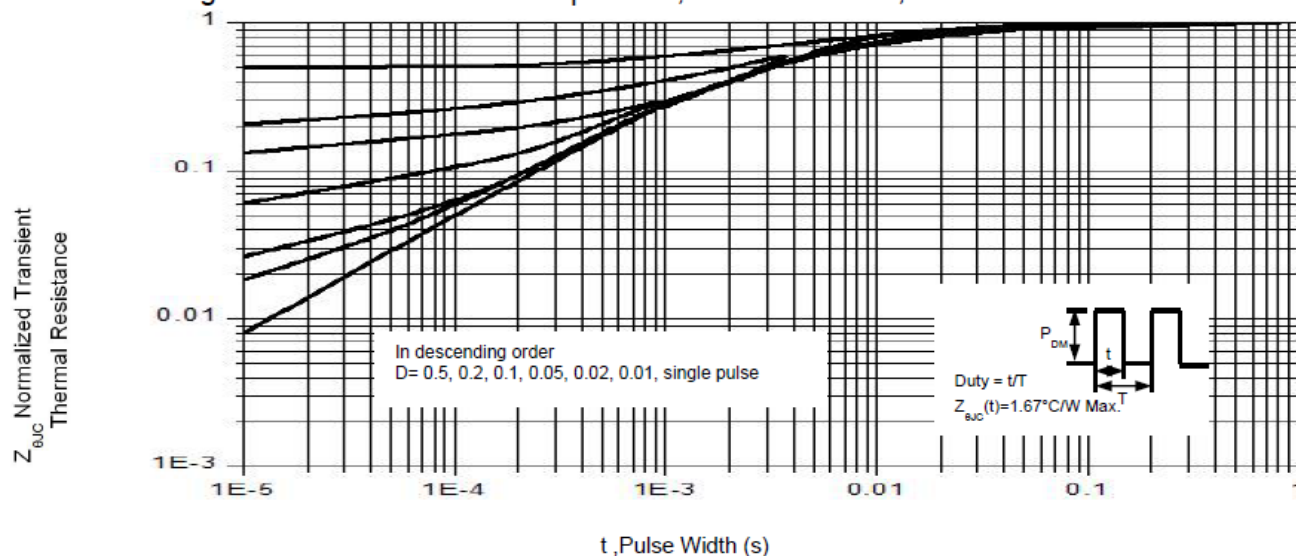
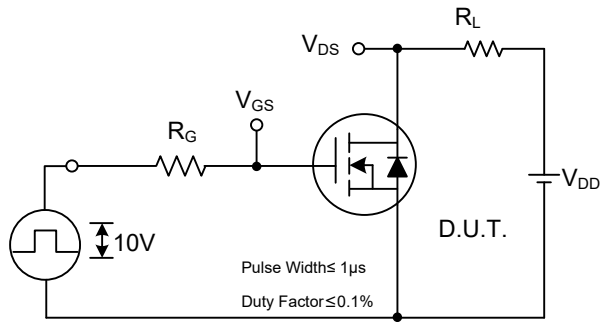
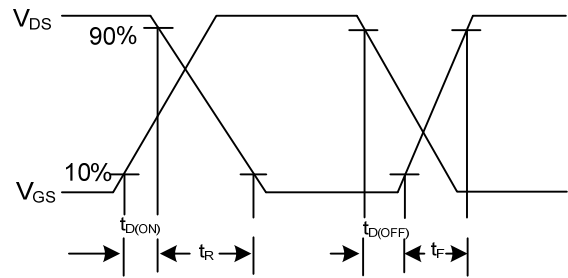


Figure 16. Transient Thermal Impedance, Junction to Case, TO-220/TO-252

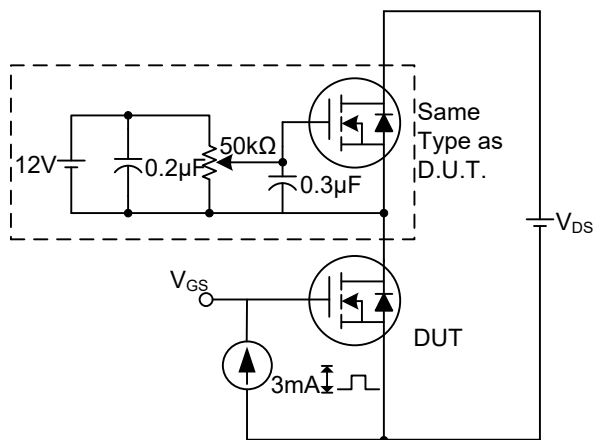




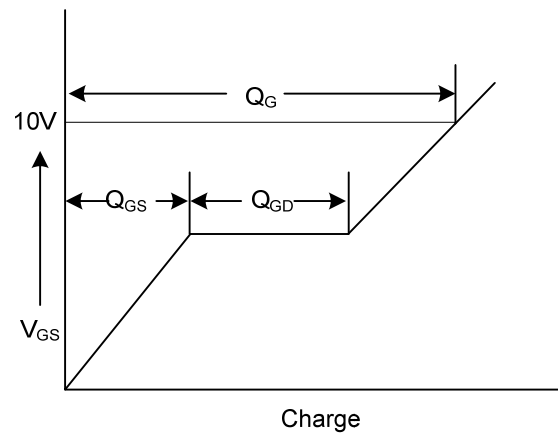
Switching Test Circuit



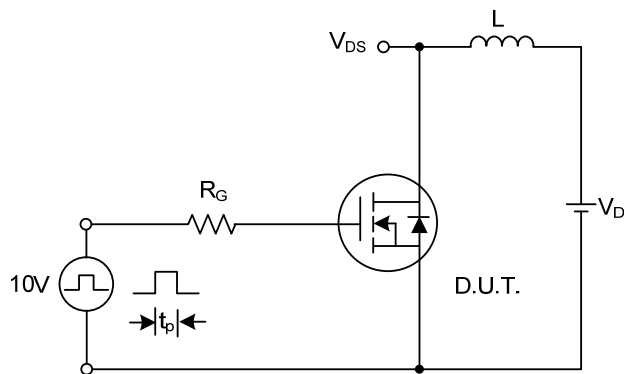
Switching Waveforms



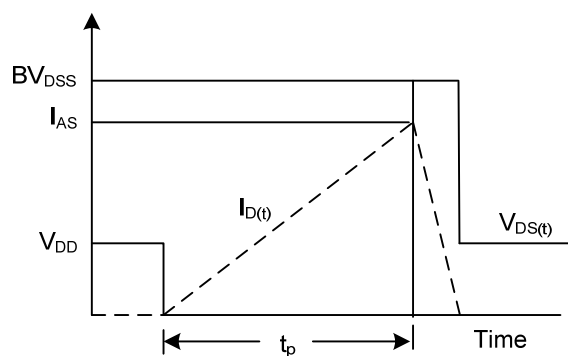
Gate Charge Test Circuit



Gate Charge Waveform



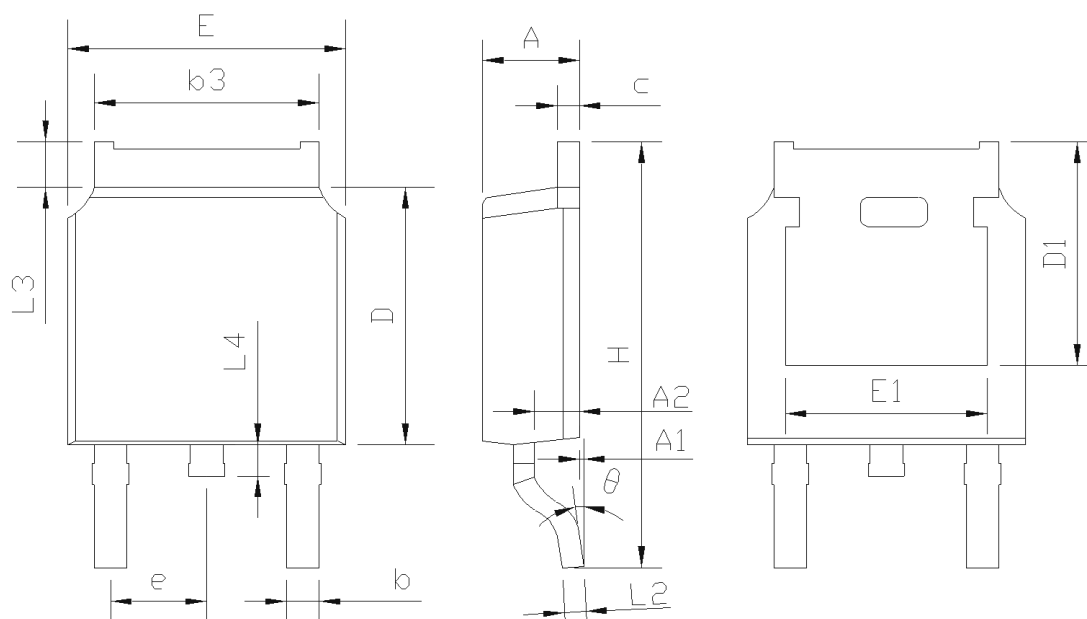
Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

The curve above is for reference only.

Mechanical Dimensions for TO-252



SYMBOL	mm		
	MIN	NOM	MAX
A	2.20	2.30	2.38
A1	0.00	-	0.20
A2	0.97	1.07	1.17
b	0.68	0.78	0.90
b3	5.20	5.33	5.46
c	0.43	0.53	0.61
D	5.98	6.10	6.22
D1	5.30REF		
E	6.40	6.60	6.73
E1	4.63	-	-
e	2.286BSC		
H	9.40	10.10	10.50
L2	0.51BSC		
L3	0.88	-	1.28
L4	0.50	-	1.00
θ	0°	-	8°

Package Marking and Ordering Information

Part Number	Marking	Package	Units/Tube	Units/Reel
MDD5N50D	5N50D	TO-252		2500